

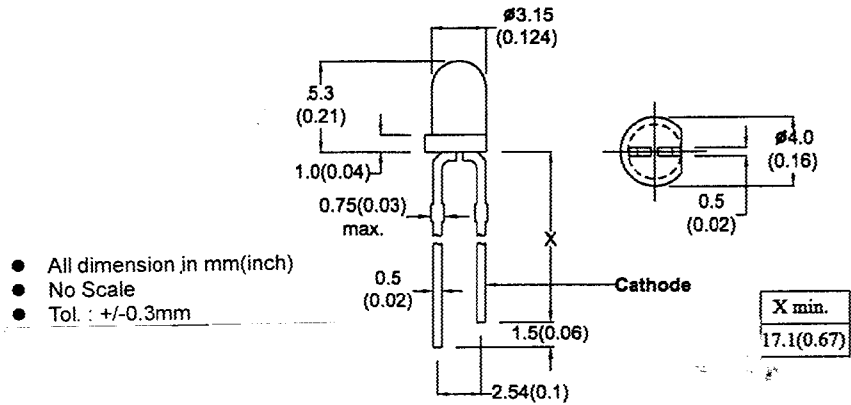
# MICRO ELECTRONICS MICRO

MI31TA

INFRARED  
EMITTING  
DIODE

## DESCRIPTION

MI31T & MIB31TA are GaAlAs infrared emitting diode molded in 3.2mm diameter clear transparent lens.



## ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	80mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	5V
Power Dissipation	150mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

\* Pulse Width = 10μs, Duty Ratio = 0.01.

## ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MI31T	MI31TA	UNIT	CONDITIONS
Radiant Power Output	MIN	1.5	1.2	mW	IF=20mA
	TYP	1.7	1.5	mW	IF=20mA
Forward Voltage	TYP	1.2	1.3	V	IF=20mA
	MAX	1.6	1.8	V	IF=20mA
Reverse Current	MAX	100	100	μA	VR=5V
Half Intensity Beam Angle	TYP	40	40	degree	IF=20mA
Peak Wavelength	TYP	940	880	nm	IF=20mA
Spectrum Line Half Width	TYP	45	70	nm	IF=20mA

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REV. A.

# MI31TA

